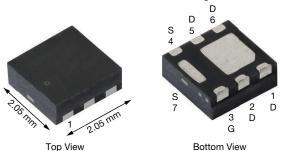
www.vishay.com

Vishay Siliconix

Automotive P-Channel 20 V (D-S) 175 °C MOSFET

PowerPAK® SC-70W-6L Single



Marking Code: QYXXXX

Configuration

PRODUCT SUMMARY V_{DS} (V) -20 0.0250 $R_{DS(on)}$ (Ω) at $V_{GS} = -4.5 \text{ V}$ $R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$ 0.0420 $I_D(A)$ -9

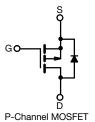
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- · Wettable flank terminals
- 100 % R_a and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SC-70W-6L
Lead (Pb)-free and halogen-free	SQA407CEJW (for detailed order number please see www.vishay.com/doc?79776)

Single

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-20	V	
Gate-source voltage		V_{GS}	± 12	V	
Continuous drain current ^a	T _C = 25 °C	1	-9		
	T _C = 125 °C	- I _D	-9		
Continuous source current (diode conduction) a		I _S	-9	Α	
Pulsed drain current ^b		I _{DM}	-36		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-15		
Single pulse avalanche energy	L = 0.1 IIIIA	E _{AS}	11.25	mJ	
Maximum power dissipation	T _C = 25 °C	D	13.6	W	
	T _C = 125 °C	P_{D}	4.5	VV	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260	J	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	R_{thJA}	90	°C/W	
Junction-to-case (drain)		R_{thJF}	11	C/VV	

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$
- c. When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components Not intended for continuous use with positive gate voltage > 3.0 V



Vishay Siliconix

PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-20	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-1.0	-1.3		
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -20 V	=	-	-1		
		V _{GS} = 0 V	V _{DS} = -20 V, T _J = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V _{DS} = -20 V, T _J = 175 °C	-	-	-150		
On-state drain current ^a	I _{D(on)}	$V_{GS} = -4.5 \text{ V}$	$V_{DS} \ge 5 V$	-8	-	-	Α	
Daile and a state of the second		V _{GS} = -4.5 V	I _D = -4.5 A	-	0.0202	0.0250	Ω	
		$V_{GS} = -4.5 \text{ V}$	I _D = -4.5 A, T _J = 125 °C	-	-	0.0337		
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}$	I _D = -4.5 A, T _J = 175 °C	=.	-	0.0381		
		V _{GS} = -2.5 V	I _D = -3 A	-	0.0338	0.0420		
Forward transconductance b	9 _{fs}	V _{DS} :	= -10 V, I _D = -4 A	-	20	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = -10 V, f = 1 MHz	-	1500	2100	pF	
Output capacitance	C _{oss}	V _{GS} = 0 V		ī	219	310		
Reverse transfer capacitance	C _{rss}	1		-	195	275		
Total gate charge c	Qg		V _{DS} = -10 V, I _D = -8 A	-	15.7	24	nC	
Gate-source charge ^c	Q _{gs}	$V_{GS} = -4.5 \text{ V}$		1	3.6	-		
Gate-drain charge ^c	Q _{gd}	1		-	4.6	-		
Gate resistance	R _g	f = 1 MHz		1.2	2.45	3.7	Ω	
Turn-on delay time ^c	t _{d(on)}			-	16	24		
Rise time ^c	t _r	V _{DD} :	$V_{DD} = -10 \text{ V}, R_1 = 4 \Omega$		22	33	ns	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -2.5 \text{ Å}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		-	29	44		
Fall time ^c	t _f			-	10	15		
Source-Drain Diode Ratings and Charact	eristics				•			
Pulsed current ^a	I _{SM}			-	-	-36	Α	
Forward voltage	V_{SD}	$I_F = -4.5 \text{ A}, V_{GS} = 0$		-	-0.81	-1.2	V	
Body diode reverse recovery time	t _{rr}			=	13	26	ns	
Body diode reverse recovery charge	Q _{rr}	I _F = -2 A, di/dt = 100 A/μs		-	6	12	nC	
Reverse recovery fall time	t _a			=-	7	-	r.	
Reverse recovery rise time	t _b			-	6		ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.8	-	Α	

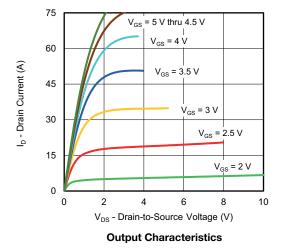
Notes

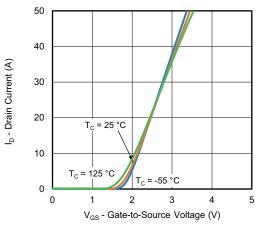
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

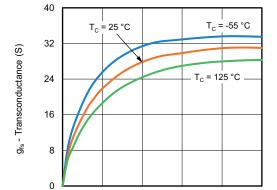
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





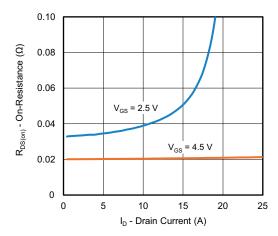


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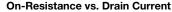


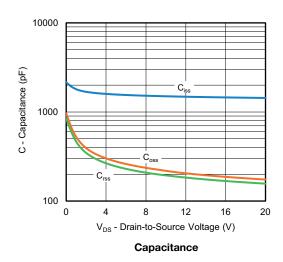
I_D - Drain Current (A) **Transconductance**

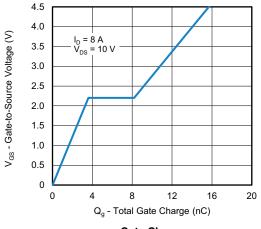
15

20

25

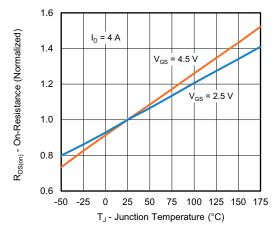




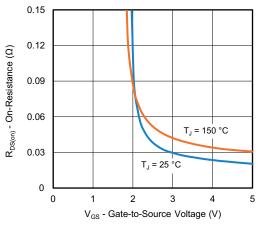




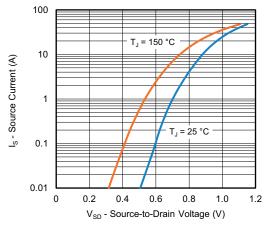
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



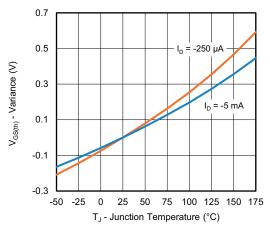
On-Resistance vs. Junction Temperature



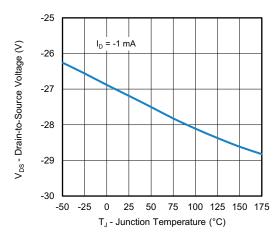
On-Resistance vs. Gate-to-Source Voltage



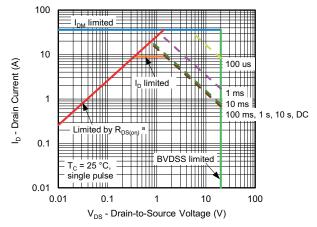
Source-Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

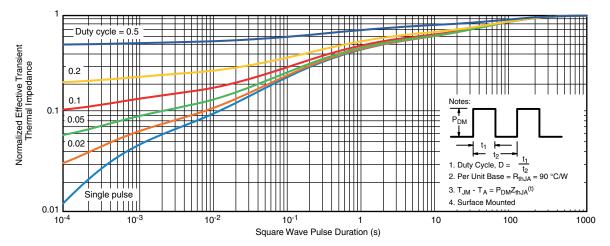
Note

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

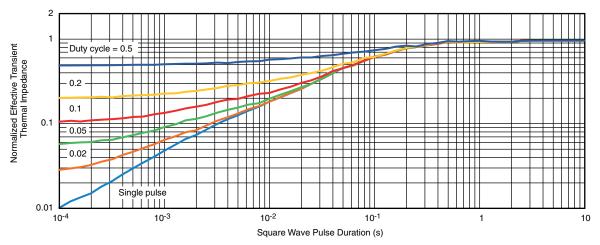
For technical questions, contact: automostech



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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